

# **1SS120**

# Silicon Epitaxial Planar Diode for High Speed Switching

REJ03G0565-0400

(Previous: ADE-208-167C)

Rev.4.00

Mar 24, 2005

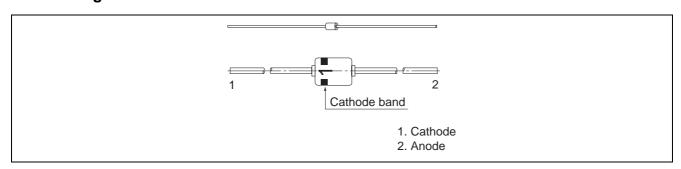
### **Features**

- Low capacitance. (C = 3.0 pF max)
- Short reverse recovery time.  $(t_{rr} = 3.5 \text{ ns max})$
- Small glass package (MHD) enables easy mounting and high reliability.

## **Ordering Information**

Type No.	Cathode band	Mark	Package Name	Package Code (Previous Code)
1SS120	Light Blue	1	MHD	GRZZ0002ZC-A
				(MHD)

## **Pin Arrangement**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit
Peak reverse voltage	V <sub>RM</sub>	70	V
Reverse voltage	V <sub>R</sub>	60	V
Average rectified current	I <sub>0</sub>	150	mA
Peak forward current	I <sub>FM</sub>	450	mA
Non-Repetitive peak forward surge current	I <sub>FSM</sub> *	1	Α
Power dissipation	Pd	250	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	−65 to +175	°C

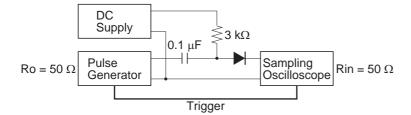
Note: Within 1s forward surge current.

## **Electrical Characteristics**

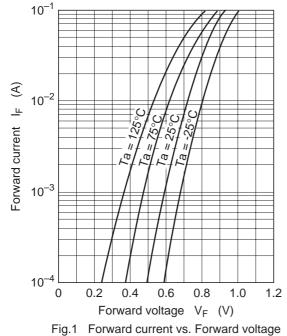
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	$V_{F}$	_	_	0.8	V	I <sub>F</sub> = 10 mA
Reverse current	I <sub>R</sub>	_	_	0.1	μΑ	V <sub>R</sub> = 60 V
Capacitance	С	_	_	3.0	pF	V <sub>R</sub> = 1 V, f = 1 MHz
Reverse recovery time	t <sub>rr</sub> *	_	_	3.5	ns	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 50 \Omega$

Note: Reverse recovery time test circuit



### **Main Characteristic**



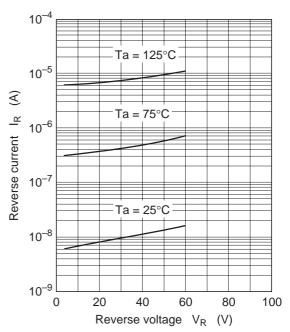
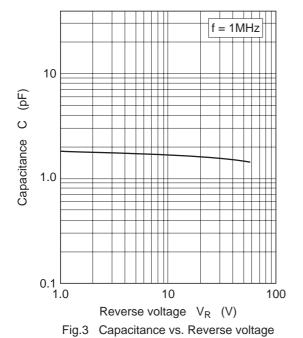
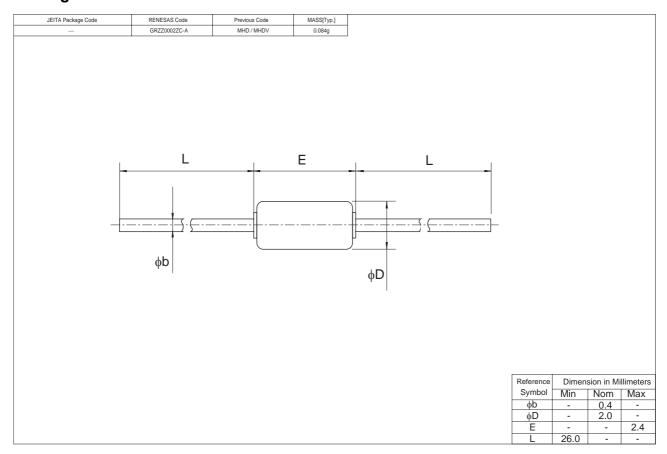


Fig.2 Reverse current vs. Reverse voltage



## **Package Dimensions**



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